MAC223A6, MAC223A8, MAC223A10

Preferred Device

Triacs

Silicon Bidirectional Thyristors

Designed primarily for full-wave ac control applications such as lighting systems, heater controls, motor controls and power supplies; or wherever full–wave silicon–gate–controlled devices are needed.

- Off–State Voltages to 800 Volts
- All Diffused and Glass Passivated Junctions for Parameter Uniformity and Stability
- Small, Rugged, Thermowatt Construction for Thermal Resistance and High Heat Dissipation
- Gate Triggering Guaranteed in Four Modes
- Device Marking: Logo, Device Type, e.g., MAC223A6, Date Code

ON Semiconductor

http://onsemi.com

**TRIACS
25 AMPERES RMS
400 thru 800 VOLTS**

MT2 — MT1, G

**TO–220AB
CASE 221A
STYLE 4**

MAXIMUM RATINGS (T$_J$ = 25°C unless otherwise noted)

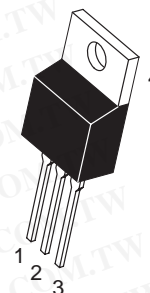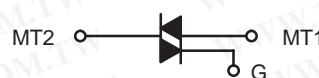| Rating	Symbol	Value	Unit
Peak Repetitive Off–State Voltage[1] (T$_J$ = –40 to 125°C, Sine Wave 50 to 60 Hz, Gate Open) MAC223A6 MAC223A8 MAC223A10	V$_{DRM}$, V$_{RRM}$	 400 600 800	Volts
On–State Current RMS Full Cycle Sine Wave 50 to 60 Hz (T$_C$ = 80°C)	I$_{T(RMS)}$	25	A
Peak Non–repetitive Surge Current (One Full Cycle, 60 Hz, T$_C$ = 80°C) Preceded and followed by rated current	I$_{TSM}$	250	A
Circuit Fusing (t = 8.3 ms)	I^{2}t	260	A^{2}s
Peak Gate Current (t ≤ 2.0 μsec; T$_C$ = +80°C)	I$_{GM}$	2.0	A
Peak Gate Voltage (t ≤ 2.0 μsec; T$_C$ = +80°C)	V$_{GM}$	± 10	Volts
Peak Gate Power (t ≤ 2.0 μsec; T$_C$ = +80°C)	P$_{GM}$	20	Watts
Average Gate Power (T$_C$ = 80°C, t = 8.3 ms)	P$_{G(AV)}$	0.5	Watts
Operating Junction Temperature Range	T$_J$	–40 to 125	°C
Storage Temperature Range	T$_{stg}$	–40 to 150	°C
Mounting Torque	—	8.0	in. lb.

(1) V$_{DRM}$ and V$_{RRM}$ for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

PIN ASSIGNMENT

1	Main Terminal 1
2	Main Terminal 2
3	Gate
4	Main Terminal 2

ORDERING INFORMATION

Device	Package	Shipping
MAC223A6	TO220AB	500/Box
MAC223A8	TO220AB	500/Box
MAC223A10	TO220AB	500/Box

Preferred devices are recommended choices for future use and best overall value.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.2	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	60	°C/W
Maximum Lead Temperature for Soldering Purposes 1/8″ from Case for 10 Seconds	T_L	260	°C

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise indicated; Electricals apply in both directions)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Peak Repetitive Blocking Current T_J = 25°C (V_D = Rated V_{DRM}, V_{RRM}; Gate Open) T_J = 125°C	I_{DRM}, I_{RRM}	— —	— —	10 2.0	μA mA
ON CHARACTERISTICS					
Peak On–State Voltage (I_{TM} = ±35 A Peak, Pulse Width ≤ 2 ms, Duty Cycle ≤ 2%)	V_{TM}	—	1.4	1.85	Volts
Gate Trigger Current (Continuous dc) (V_D = 12 V, R_L = 100 Ω) MT2(+), G(+); MT2(−), G(−); MT(+), G(−) MT2(−), G(+)	I_{GT}	 — —	 20 30	 50 75	mA
Gate Trigger Voltage (Continuous dc) (V_D = 12 V, R_L = 100 Ω) MT2(+), G(+); MT2(−), G(−); MT(+), G(−) MT2(−), G(+)	V_{GT}	 — —	 1.1 1.3	 2.0 2.5	Volts
Gate Non–trigger Voltage (V_D = 12 V, T_J = 125°C, R_L = 100 Ω) All Quadrants	V_{GD}	0.2	0.4	—	Volts
Holding Current (V_D = 12 Vdc, Gate Open, Initiating Current = ±200 mA)	I_H	—	10	50	mA
Turn–On Time (V_D = Rated V_{DRM}, I_{TM} = 35 A Peak, I_G = 200 mA)	t_{gt}	—	1.5	—	μs
DYNAMIC CHARACTERISTICS					
Critical Rate of Rise of Off-State Voltage (V_D = Rated V_{DRM}, Exponential Waveform, T_C = 125°C)	dv/dt	—	40	—	V/μs
Critical Rate of Rise of Commutation Voltage (V_D = Rated V_{DRM}, I_{TM} = 35 A Peak, Commutating di/dt = 12.6 A/ms, Gate Unenergized, T_C = 80°C)	dv/dt(c)	—	5.0	—	V/μs

Voltage Current Characteristic of Triacs
(Bidirectional Device)

Symbol	Parameter
V_{DRM}	Peak Repetitive Forward Off State Voltage
I_{DRM}	Peak Forward Blocking Current
V_{RRM}	Peak Repetitive Reverse Off State Voltage
I_{RRM}	Peak Reverse Blocking Current
V_{TM}	Maximum On State Voltage
I_H	Holding Current

+ Current

Quadrant 1
MainTerminal 2 +

V_{TM}

on state

I_H

I_{RRM} at V_{RRM}

off state

+ Voltage

I_{DRM} at V_{DRM}

I_H

Quadrant 3
MainTerminal 2 −

V_{TM}

Quadrant Definitions for a Triac

MT2 POSITIVE
(Positive Half Cycle)
+

(+) MT2

Quadrant II

(−) I_{GT}
GATE

MT1

REF

(+) MT2

(+) I_{GT}
GATE

MT1

REF

Quadrant I

I_{GT} −

+ I_{GT}

(−) MT2

Quadrant III

(−) I_{GT}
GATE

MT1

REF

(−) MT2

(+) I_{GT}
GATE

MT1

REF

Quadrant IV

−
MT2 NEGATIVE
(Negative Half Cycle)
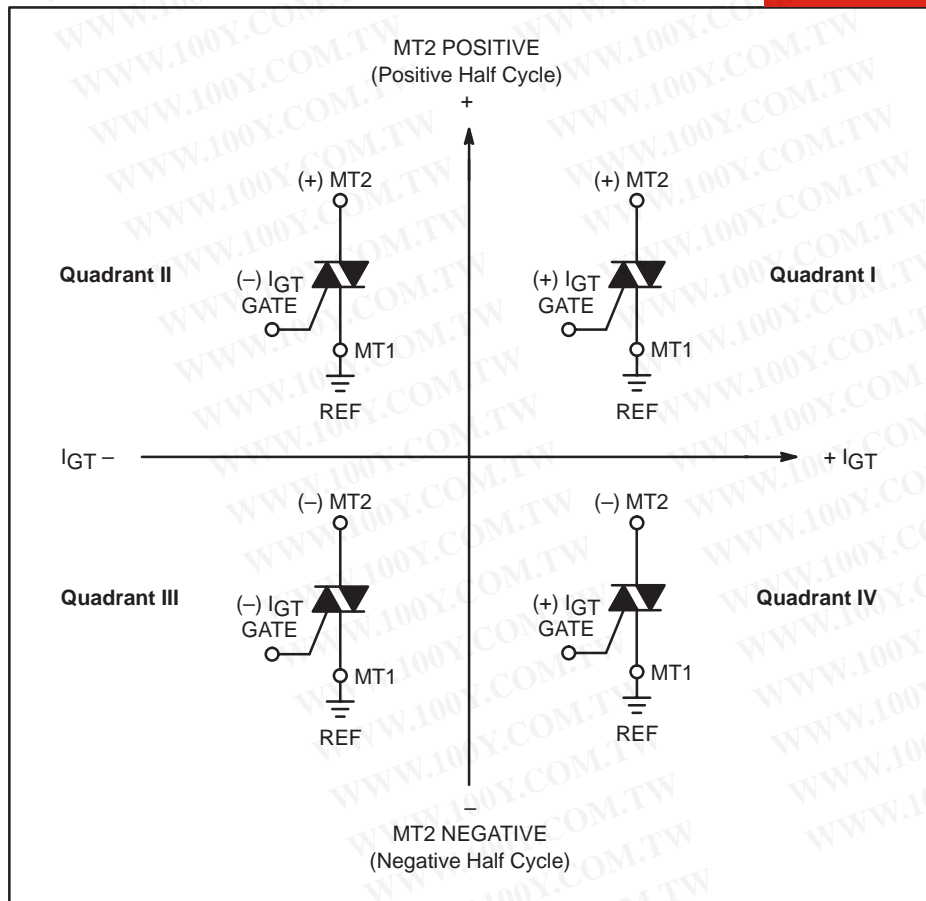
All polarities are referenced to MT1.
With in–phase signals (using standard AC lines) quadrants I and III are used.
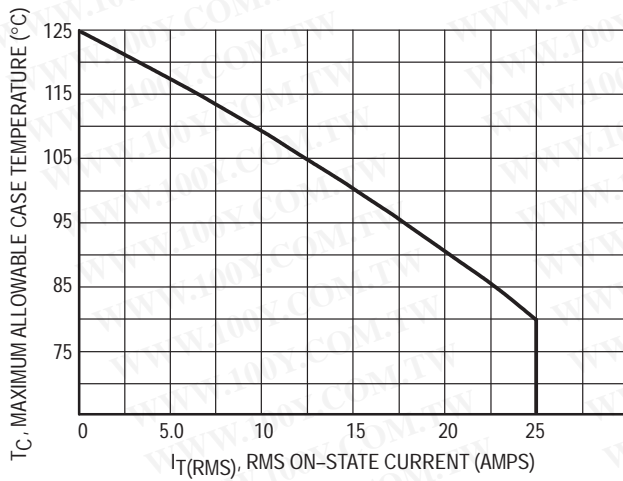
Figure 1. RMS Current Derating
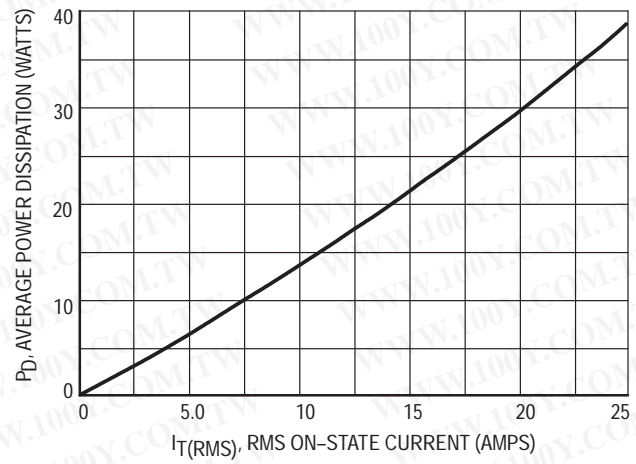
Figure 2. On–State Power Dissipation
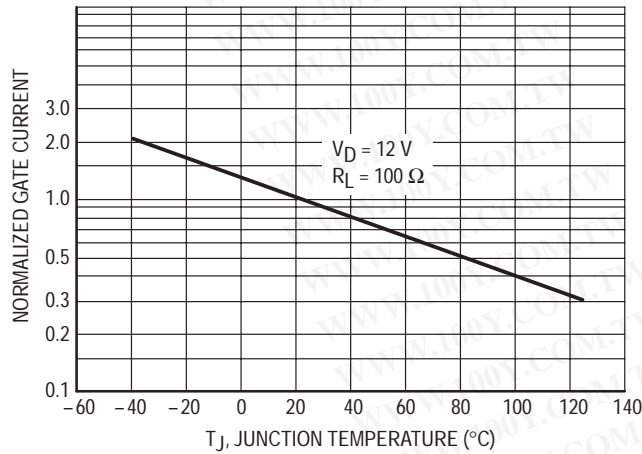
Figure 3. Typical Gate Trigger Current
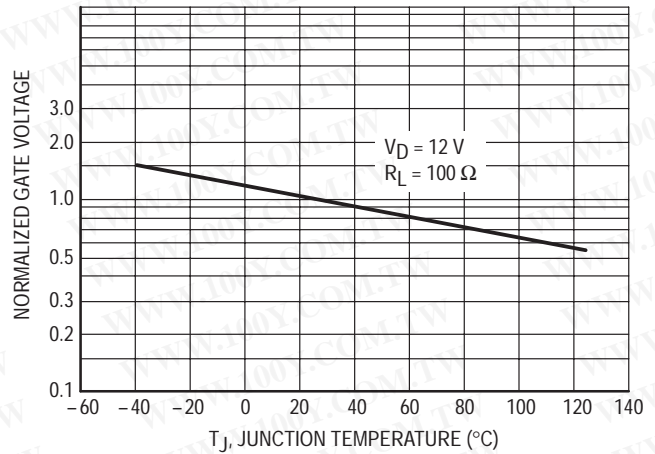
Figure 4. Typical Gate Trigger Voltage
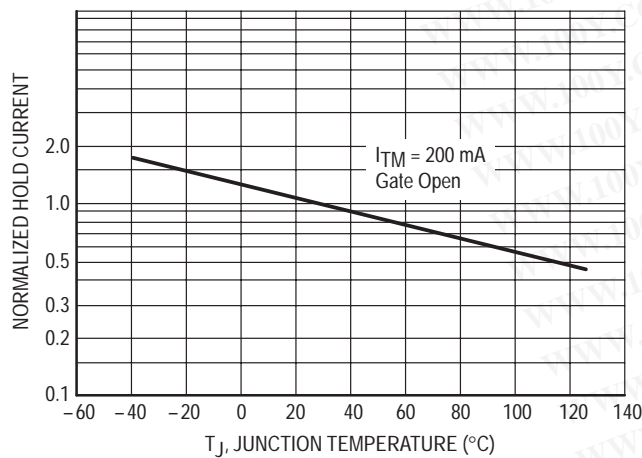
Figure 5. Typical Hold Current
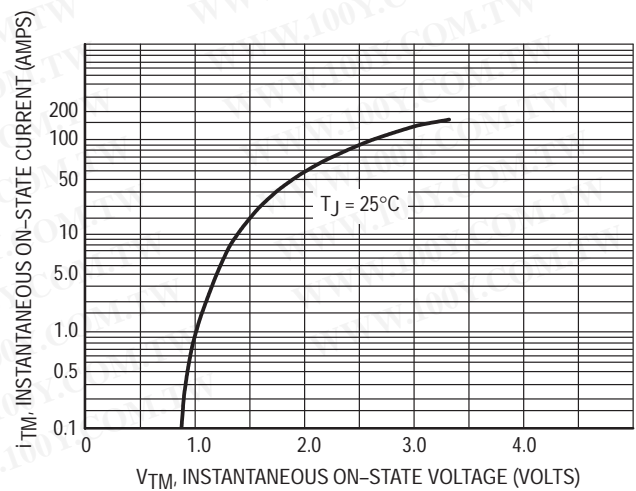
Figure 6. Typical On–State Characteristics

PACKAGE DIMENSIONS

TO–220AB
CASE 221A–07
ISSUE Z
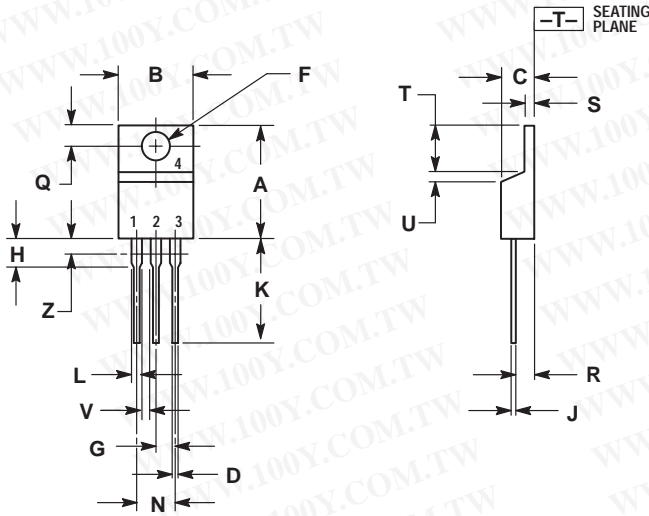
NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
H	0.110	0.155	2.80	3.93
J	0.014	0.022	0.36	0.55
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	–––	1.15	–––
Z	–––	0.080	–––	2.04

STYLE 4:
PIN 1. MAIN TERMINAL 1
    2. MAIN TERMINAL 2
    3. GATE
    4. MAIN TERMINAL 2

Notes

<u>Notes</u>

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胜特力电子(深圳) 86-755-83298787
Http://www.100y.com.tw

PUBLICATION ORDERING INFORMATION